imall

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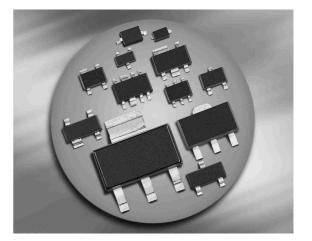




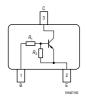
PNP Silicon Digital Transistor

- Switching circuit, inverter, interface circuit, driver circuit
- Built in bias resistor (R_1 = 22 k Ω , R_2 = 22 k Ω)
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101





BCR191 BCR191W



Туре	Marking	Pin Configuration					Package	
BCR191	WOs	1=B	2=E	3=C	-	-	-	SOT23
BCR191W	WOs	1=B	2=E	3=C	-	-	-	SOT323

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V _{CEO}	50	V
Collector-base voltage	V _{CBO}	50	
Input forward voltage	V _{i(fwd)}	60	
Input reverse voltage	V _{i(rev)}	10	
Collector current	I _C	100	mA
Total power dissipation-	P _{tot}		mW
BCR191, <i>T</i> _S ≤ 102°C		200	
BCR191W, <i>T</i> _S ≤ 124°C		250	
Junction temperature	Tj	150	°C
Storage temperature	T _{stg}	-65 150	



Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R _{thJS}		K/W
BCR191		≤ 240	
BCR191W		≤ 105	

Electrical Characteristics at $T_A = 25^{\circ}$ C, unless otherwise specified

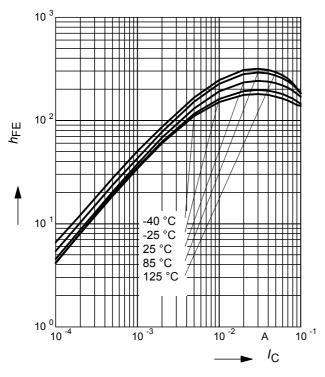
Parameter	Symbol		Unit		
			typ.	max.	
DC Characteristics			1	T	
Collector-emitter breakdown voltage	V _{(BR)CEO}	50	-	-	V
<i>I</i> _C = 100 μA, <i>I</i> _B = 0					
Collector-base breakdown voltage	V _{(BR)CBO}	50	-	-	
$I_{\rm C}$ = 10 µA, $I_{\rm E}$ = 0					
Collector-base cutoff current	I _{CBO}	-	-	100	nA
$V_{\rm CB}$ = 40 V, $I_{\rm E}$ = 0					
Emitter-base cutoff current	I _{EBO}	-	-	350	μA
V _{EB} = 10 V, <i>I</i> _C = 0					
DC current gain ²⁾	h _{FE}	50	-	-	-
<i>I</i> _C = 5 mA, <i>V</i> _{CE} = 5 V					
Collector-emitter saturation voltage ²⁾	V _{CEsat}	-	-	0.3	V
<i>I</i> _C = 10 mA, <i>I</i> _B = 0.5 mA					
Input off voltage	V _{i(off)}	0.8	-	1.5	
<i>I</i> _C = 100 μA, <i>V</i> _{CE} = 5 V					
Input on voltage	V _{i(on)}	1	-	2.5	
$I_{\rm C}$ = 2 mA, $V_{\rm CE}$ = 0.3 V					
Input resistor	R ₁	15	22	29	kΩ
Resistor ratio	R ₁ /R ₂	0.9	1	1.1	-
AC Characteristics					
Transition frequency	f _T	-	200	-	MHz
<i>I</i> _C = 10 mA, <i>V</i> _{CE} = 5 V, <i>f</i> = 100 MHz					
Collector-base capacitance	C _{cb}	-	3	-	pF
V _{CB} = 10 V, <i>f</i> = 1 MHz					
	I		I	ı	

¹For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)

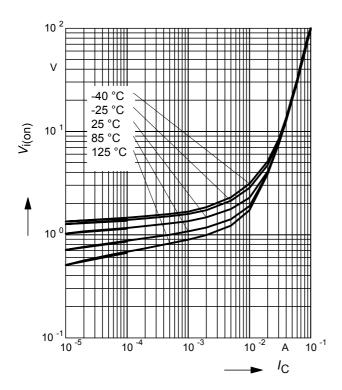
²Pulse test: t < 300µs; D < 2%



DC current gain $h_{FE} = f(I_C)$ $V_{CE} = 5 V$ (common emitter configuration)

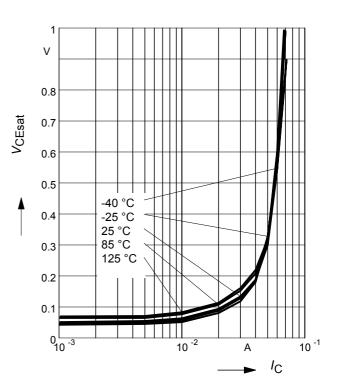


Input on Voltage $V_{i(on)} = f(I_C)$ $V_{CE} = 0.3V$ (common emitter configuration)

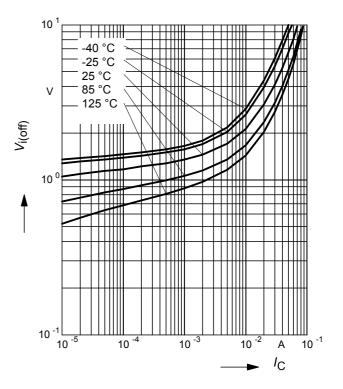


Collector-emitter saturation voltage

 $V_{\text{CEsat}}=f(I_{\text{C}}),\,I_{\text{C}}/I_{\text{B}}=20$

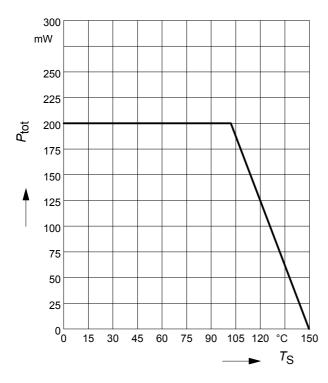


Input off voltage $V_{i(off)} = f(I_C)$ $V_{CE} = 5V$ (common emitter configuration)

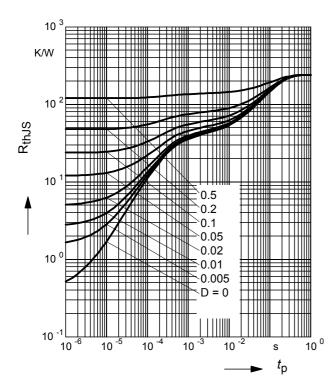




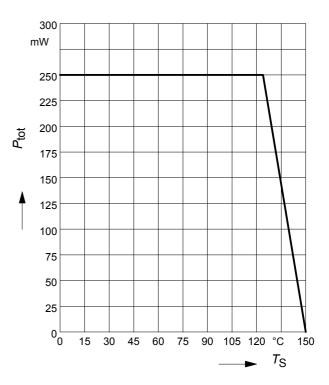
Total power dissipation $P_{tot} = f(T_S)$ BCR191



Permissible Pulse Load $R_{thJS} = f(t_p)$ BCR191

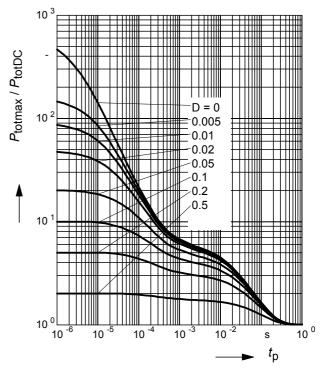


Total power dissipation $P_{tot} = f(T_S)$ BCR191W



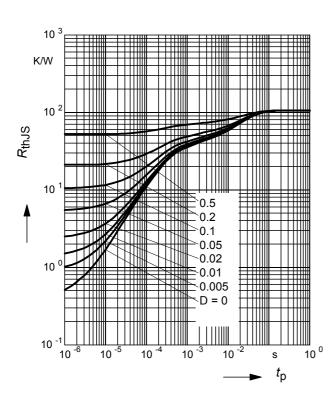
Permissible Pulse Load

 $P_{\text{totmax}}/P_{\text{totDC}} = f(t_{\text{p}})$ BCR191



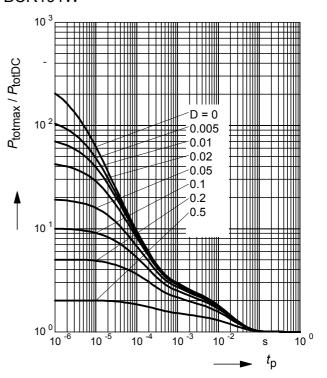


Permissible Puls Load $R_{\text{thJS}} = f(t_p)$ BCR191W

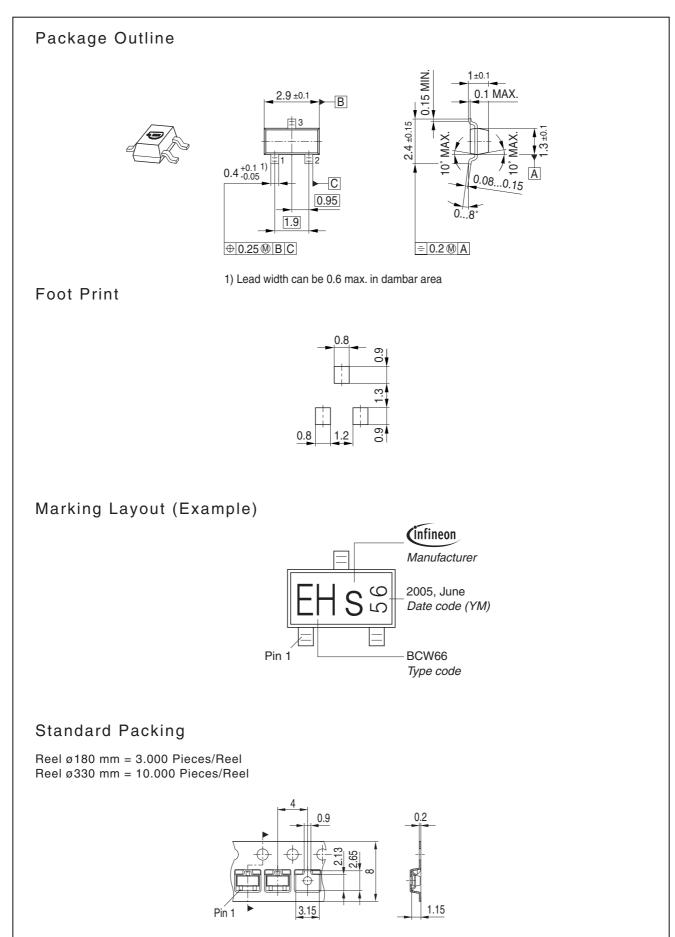


Permissible Pulse Load

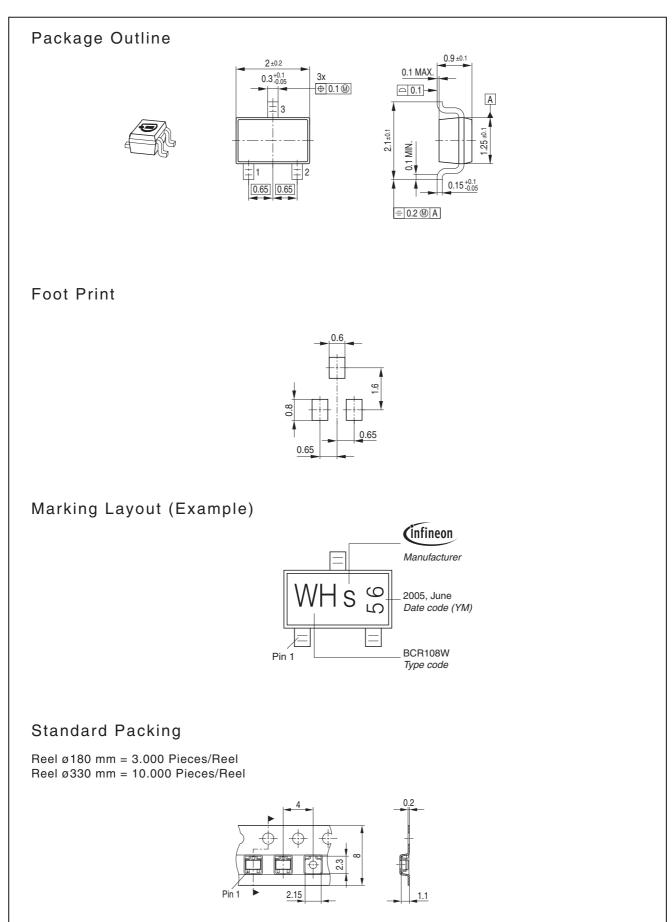
 $P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$ BCR191W















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